

Title (en)
BATCH FABRICATED 3D INTERCONNECT

Title (de)
Simultanherstellung von 3D-Interconnects

Title (fr)
Interconnexion 3D fabriquée par lots

Publication
EP 2455968 A1 20120523 (EN)

Application
EP 11190204 A 20111122

Priority
• US 41648510 P 20101123
• US 201113299576 A 20111118

Abstract (en)
In an example, a method of fabricating one or more vertical interconnects is provided. The method includes patterning and stacking a plurality of wafers to form a wafer stack. A plurality of apertures can be formed in the wafer stack within one or more saw streets of the wafer stack, and conductive material can be deposited on sidewalls of the plurality of apertures. The wafer stack can be diced along the one or more saw streets and through the plurality of apertures such that the conductive material on the sidewalls is exposed on an edge portion of resulting stacked dies

IPC 8 full level
H01L 21/768 (2006.01); **G01C 19/5783** (2012.01); **G01P 15/18** (2013.01); **H01L 25/065** (2006.01)

CPC (source: EP US)
H01L 21/76898 (2013.01 - EP US); **H01L 24/24** (2013.01 - EP US); **H01L 24/94** (2013.01 - EP US); **H01L 24/97** (2013.01 - EP US); **H01L 25/0657** (2013.01 - EP US); **H01L 25/50** (2013.01 - EP US); **H01L 24/02** (2013.01 - EP US); **H01L 24/32** (2013.01 - EP US); **H01L 24/92** (2013.01 - EP US); **H01L 2224/02375** (2013.01 - EP US); **H01L 2224/32145** (2013.01 - EP US); **H01L 2224/9202** (2013.01 - EP US); **H01L 2224/92244** (2013.01 - EP US); **H01L 2224/97** (2013.01 - EP US); **H01L 2225/06541** (2013.01 - EP US); **H01L 2225/06551** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01322** (2013.01 - EP US); **H01L 2924/014** (2013.01 - EP US); **H01L 2924/12042** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/1433** (2013.01 - EP US); **H01L 2924/1461** (2013.01 - EP US)

Citation (search report)
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Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
EP 2455968 A1 20120523; CN 102556948 A 20120711; JP 2012183631 A 20120927; US 2012126350 A1 20120524

DOCDB simple family (application)
EP 11190204 A 20111122; CN 201110461892 A 20111123; JP 2011255389 A 20111122; US 201113299576 A 20111118